

HSK122

Silicon Epitaxial Planar Diode for High Voltage Switching

HITACHI

Rev. 2
Aug. 1995

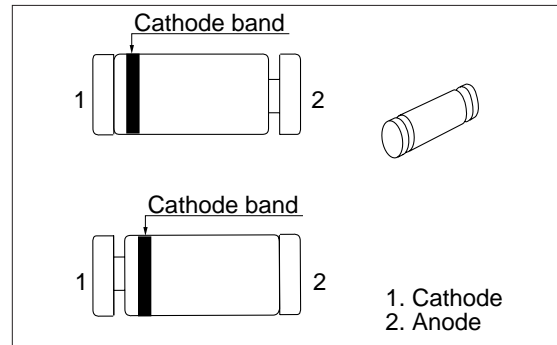
Features

- High reverse voltage. ($V_R = 400V$)
- LLD package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Cathode band	Package code
HSK122	Orange	LLD

Outline



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	410	V
Reverse voltage	V_R	400	V
Peak forward current	I_{FM}	625	mA
Non-Repetitive peak forward surge current	I_{FSM}^*	1	A
Average forward current	I_O	150	mA
Junction temperature	T_j	175	$^\circ C$
Storage temperature	T_{stg}	-65 to +175	$^\circ C$

* Within 1s forward surge current.

Electrical Characteristics ($T_a = 25^\circ C$)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.2	V	$I_F = 100 \text{ mA}$
Reverse current	I_R	—	—	1.0	μA	$V_R = 400 \text{ V}$
Capacitance	C	—	—	10	pF	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$
Reverse recovery time	t_{rr}	—	—	10	μs	$I_F = 30 \text{ mA}, V_R = 10 \text{ V}, R_L = 2 \text{ k}\Omega$

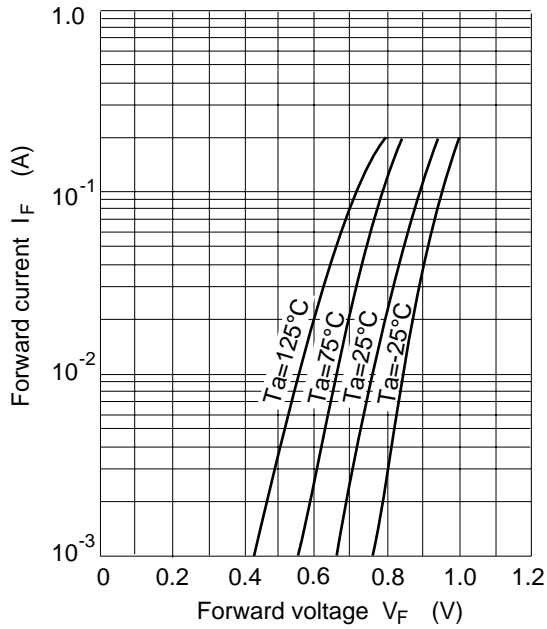


Fig.1 Forward current Vs. Forward voltage

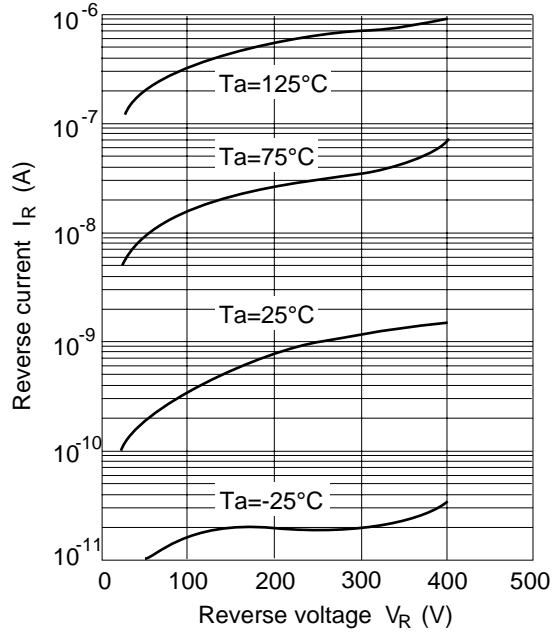


Fig.2 Reverse current Vs. Reverse voltage

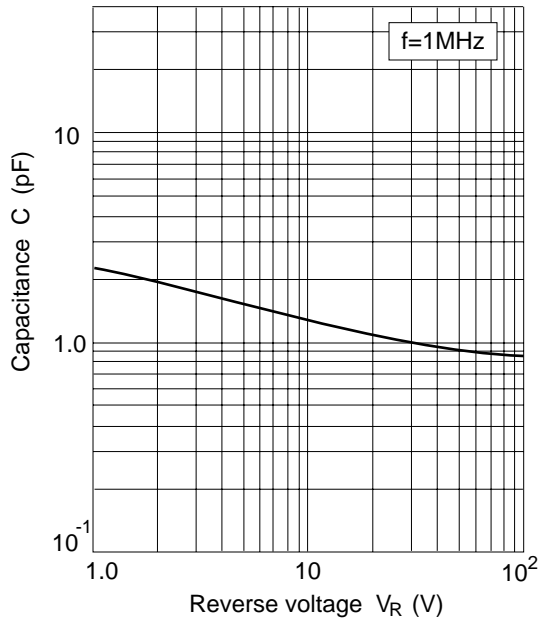
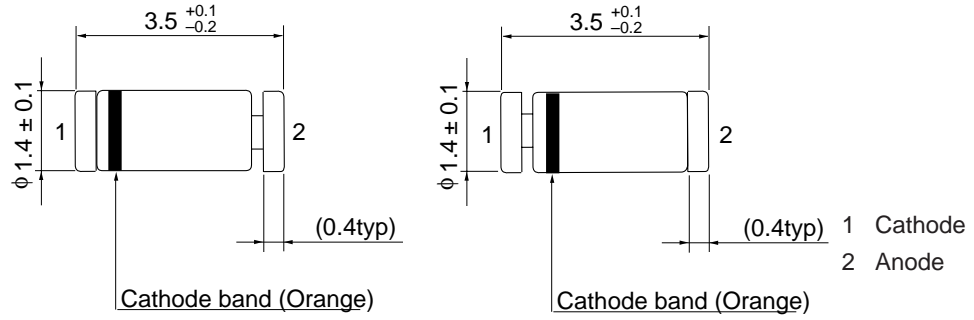


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



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HITACHI Code	LLD
JEDEC Code	—
EIAJ Code	—
Weight (g)	0.027